

Citations for Ion : S

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1966	Bethge, K. Sandner, P. Schmidt, H. 'Energieverluste und Ladungszustände Schwerer Ionen Beim Durchgang Durch Materie' <i>Z. Naturforschg. 21A, 1052-57 (1966)</i> Comment : S. 5-20 MeV B, 5-30 MeV O, 7-28 MeV N, 5-30 MeV S -> Ni, Ag, Au	1966-Beth
1966	Fastrup, B. Hvelplund, P. Sautter, C. A. 'Stopping Cross Section in Carbon of 0.1-1.0 MeV Atoms with $5 < Z < 20$ ' <i>Kgl. Danske Videnskab. Selskab. Mat. Fys. Medd., 35, No. 10, 1-28 (1966)</i> Comment : S. (80-900 keV) H, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar -> C	1966-Fast
1968	Armitage, B. H. Hooton, B. W. 'Energy Loss of Oxygen and Sulphur Ions in Matter' <i>Nucl. Inst. Methods, 58, 29-35 (1968)</i> Comment : S. 10-30 MeV O, 19-40 MeV S -> Ag, Au	1968-Armi
1968	Bowman, W. W. Lanzafame, F. M. Cline, C. K. Yu, Yu-Wen Blann, M. 'Recoil Ranges of 0.2 - 5.2 MeV Ions in Vanadium, Nickel, Iron, Zirconium and Gold.' <i>Phys. Rev., 165, 485-93 (1968)</i> Comment : R, dR. Ion(ZI=12-81, E=0.22-5.2 MeV) -> V, Ni, Zr, Au	1968-Bowm
1968	Fastrup, B. Borup, A. Hvelplund, P. 'Stopping Cross Section in Atmospheric Air of 0.2 - 0.5 MeV Atoms with $6 \leq Z1 \leq 24$ ' <i>Can. J. Phys., 46, 489-95 (1968)</i> Comment : S. (100-1000 keV) C, N, O, Ne, N, Mg, P, S, Cl, Sc, Ca, Ti Al, Ar, K, Cr -> Air	1968-Fast
1968	Pierce, T. E. Blann, M. 'Stopping Powers and Ranges of 5-90 MeV S32, Cl35, Br79, and I127 Ions in H2, He, N2, Ar, and Kr: a Semiempirical Stopping Power Theory for Heavy Ions in Gases and Solids' <i>Phys. Rev., 173, 390-405 (1968)</i> Comment : S. 5-90 MeV 32S, 35Cl, 79Br, 127I -> H2, He, N2, Ar, Kr	1968-Pier
1968	Pierce, T. E. Bowman, W. W. Blann, M. 'Stopping Power of S32, Cl35, Br79 and I127 Ions in Mylar' <i>Phys. Rev., 172, 287-91 (1968)</i> Comment : S. 15-95 MeV 32S, 35Cl, 30-90 MeV 79Br, 60-105 MeV 127I -> Mylar	1968-Pier2
1969	Bottiger, J. Bason, F. 'Energy Loss of Heavy Ions Along Low-Index Directions in Gold Single Crystals' <i>Rad. Effects, 2, 105-10 (1969)</i> Comment : S. (300-970 keV) N, Ne, Na, Mg, S, Cl, Ar, K, Si, Mn, Fe, Kr, Y, Mo, Ag, Cd, Sb, Xe -> Au	1969-Bott

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1969	Macdonald, J. R. Sidenius, G. 'The Total Ionization in Methane of Ions with $1 \leq Z_1 \leq 20$ at Energies from 10 to 120 keV' <i>Phys. Letters A</i> , 28, 543-44 (1969) Comment : S. 10-120 keV H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, Ca, V, Sc, Ti -> CH4	1969-Macd
1970	Dearnaley, G. Wilkens, M. A. Goode, P. D. Freeman, J. H. Gard, G. A. 'The Range Distribution of Radioactive Ions Implanted into Silicon Crystals' <i>W. Palmer, M. W. Thompson, P. D. Townsend: Atomic Collision Phenomena in Solids. North-Holland, Amsterdam, P. 623-55 (1970)</i> Comment : R, dR. 40-120 keV P, Na, S, Cu, Kr -> Si, Cryst. and Amorph.	1970-Dear2
1970	Whitton, J. L. Carter, G. 'The Implantation Profiles of Energetic Heavy Ions in GaAs, GaP, and Ge' <i>W. Palmer, M. W. Thompson, P. D. Townsend: Atomic Collision Phenomena in Solids. North-Holland, Amsterdam, 615-32 (1970)</i> Comment : R, dR. 10-40 keV S, Kr, Na -> GaAs,	1970-Whit
1971	Dearnaley, M. A. Wilkins, M. A. Goode, P. D. 'Non-Gaussian Implantation Profiles' <i>Intl. Conf. Ion Implantation in Semiconductors, Ed. by I. Ruge and J. Graul, 439-454 (1971)</i> Comment : R. 40-120 keV S, P -> Si	1971-Dear
1971	Whitton, J. L. Bellavance, G. R. 'Ion Implantation of Sulphur into GaAs, GaP and Ge Monocrystals' <i>Rad. Effects</i> , 9, 127-31 (1971) Comment : R, dR. 20-40 keV S -> GaAs (Cryst. Axial And Random)	1971-Whit
1975	Bill, U. Sizmann, R. Varelas, C. Rehn, K. E. 'Transition of Axial to Planar Channeling' <i>Rad. Effects</i> , 27, 59-66(1975) Comment : S, dS. 100 MeV S -> Si (Cryst.)	1975-Bill
1975	Lyons, R. P. Ehret, . E. Park, Y. S. 'Ion Implantation of Diatomic Sulphur into GaAs' <i>Bull. Am. Phys. Soc.</i> , 20, 318 (1975) Comment : R. About 100 keV S2 -> GaAs.	1975-Lyon
1976	Comas, J. Plew, L. 'Beryllium and Sulfur Ion-Implanted Profiles in GaAs' <i>J. Elec. Mater.</i> , 5, 209-221 (1976) Comment : R. 100, 200 keV Be, S -> GaAs	1976-Coma

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1976	Eisen, F. H. Welch, B. M. 'Radiotracer Profiles in Sulfur Implanted GaAs' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 97-106 (1976)</i> <i>Comment : R. 100 keV 35S -> GaAs</i>	1976-Eise
1976	Forster, J. S. Ward, D. Andrews, H. R. Ball, G. C. Costa, G. J. 'Stopping Power Measurements for 19F, 24Mg, 27Al, 32S and 35Cl at Energies 0.2 to 3.5 MeV/Nucleon in Ti, Fe, Ni, Cu, Ag and Au.' <i>Nucl. Inst. Methods, 136, 349-59 (1976).</i> <i>Comment : S. 2.2 MeV H, 0.2-3.5 MeV/amu F, Mg, Al, S, Cl -> Ti, Fe, Ni, Cu, Ag, Au</i>	1976-Fors
1976	Grob, A. Grob, J. J. Siffert, P. 'Energy Loss and Straggling of Heavy Ions by Nuclear Interactions in Silicon' <i>Nucl. Inst. Methods, 132, 273-79 (1976)</i> <i>Comment : S, dS, Eta(Epsilon). 300-2000 keV C, N, O, Ne, Si, S, Ar -> Si</i>	1976-Grob
1977	Anttila, A. Bister, M. Fontell, A. Winterbon, K. B. 'Ranges of Some Light Ions Measured by (p,gamma) Resonance Broadening' <i>Rad. Effects, 33, 13-19 (1977)</i> <i>Comment : R. 20-100 keV 13C, 23Na, 26Mg, 27Al, 34S -> Ta; 29Si -> Al</i>	1977-Antt
1977	Molnar, B. Kennedy, T. A. 'GaAs Ion-Implantation Parameters Studied through Contactless Mobility Measurements' <i>Electrochem. Soc. Extended Abstracts, 261-262, May (1977)</i> <i>Comment : R. 120 keV S -> GaAs</i>	1977-Moln
1978	Alexander, T. K. Forster, J. S. Ball, G. C. Davies, W. G. Winterbon, K. B. 'Z1 and Z2 Variations in the Stopping Powers of Z1=10-18 Ions Deduced from DSAM Lifetime Measurements' <i>Phys. Letters, 74B, 183-186 (1978)</i> <i>Comment : S. Ne, Na, Mg, Al, Si, P, S, Ar (3-4 MeV) -> Cu, Ni, Ta, Au, Mg, Ca, Ti, Ba. Doppler shift lifetime measurements.</i>	1978-Alex
1979	Andrews, H. R. Lennard, W. N. Mitchell, I. V. Ward, D. Phillips, D. 'Low Energy Stopping Powers Determined by Time of Flight Techniques' <i>IEEE Trans. Nucl. Sci., NS-26, 1326-1330 (1979)</i> <i>Comment : S. (0.180 <vel.< 0.219 cm/ns) (6 <= Z1 <= 20)-> C, Al, Ni, Ag, Au</i>	1979-Andr
1979	Lorenzo, J. P. Davies, D. E. Ryan, T. G. 'Anodic Oxidation and Electrical Carrier Concentration Profiles of Ion-Implanted InP' <i>J. Electrochem. Soc., 126, 118-121 (1979)</i> <i>Comment : R, dR. 1 MeV S, Si -> InP</i>	1979-Lore

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1979	Magee, C. W. 'Depth Profiling of N-Type Dopants in Si and GaAs using Cs+ Bombardment Negative Secondary Ion Mass Spectrometry in Ultrahigh Vacuum' <i>J. Electrochem. Soc.</i> , 126, 660-663 (1979) <i>Comment</i> : R, dR. 15 keV H, 80 keV P, 200 keV As -> Si; 200 keV Si, 250 keV S -> GaAs	1979-Mage
1979	Park, Y. S. Grant, J. T. Haas, T. W. 'The Determination of Sulfur-Ion-Implantation Profiles in GaAs using Auger Electron Spectroscopy' <i>J. Appl. Phys.</i> , 50, 809-812 (1979) <i>Comment</i> : R, dR. 60, 120 keV S+, S2+ -> GaAs	1979-Park
1979	Santry, D. C. Werner, R. D. Westcott, O. M. 'The Range of 120 keV Ions in Solids' <i>IEEE Trans. Nucl. Sci.</i> , Ns-26, 1331-1334 (1979) <i>Comment</i> : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si	1979-Sant
1979	Ward, D. Andrews, H. R. Mitchell, I. V. Lennard, W. N. Walker, R. B. 'Systematics for the Z1-Oscillation in Stopping Powers of Various Solid Materials' <i>Can. J. Phys.</i> , 57, 645-656 (1979). <i>Comment</i> : S. (vel.=0.18-0.22 cm/ns) C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Ca -> C, Al, Ni, Ag, Au	1979-Ward
1980	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. 'Charge-Exchange Effects in Energy-Loss Straggling' <i>Nucl. Inst. Methods</i> , 170, 221-225 (1980) <i>Comment</i> : R, dR. 0-50 MeV Atomic Numbers 1-16 -> Al	1980-Sofi
1983	Wilson, R. G. Jamba, D. M. Deline, V. R. Evans, C. A. Park, Y. S. 'Depth Distributions of Sulfur Implanted into GaAs as a Function of Ion Energy, Ion Fluence, and Annealing Temperature and Encapsulation' <i>J. Appl. Phys.</i> , 54, 3849-3854 (1983) <i>Comment</i> : R. S (40-600 keV) -> GaAs	1983-Wils
1986	Lennard, W. N. Geissel, H. Phillips, D. Jackson, D. P. 'Heavy Ion Straggling: Possible Evidence for Inner-Shell Excitation' <i>Phys. Rev. Letters</i> , 57, 318-320 (1986) <i>Comment</i> : dS.F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Sc (16 keV/amu) -> C	1986-Lenn
1988	Gardes, D. Bimbot, R. DellaNegra, S. Dumail, M. Kubica, B. 'Interaction of Heavy Ion Beams with a Hydrogen Plasma: Plasma Lens Effect and Stopping Power Enhancement' <i>Europhys. Lett.</i> , 8, 701-705 (1988) <i>Comment</i> : S. C, S (2 MeV/amu) -> H (plasma)	1988-Gard

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1988	Wilson, R. G. '(111) Random and (110) Channeling Implantation Profiles and Range Parameters in HgCdTe' <i>J. Appl. Phys.</i> , 63 , 5302-5311 (1988) <i>Comment</i> : R, dR. 45 Ions (H to Ta) at 100-700 keV -> HgCdTe	1988-Wils
1988	Wilson, R. G. 'Ion Implantation and SIMS Profiling of Impurities in II-VI Materials HgCdTe and CdTe' <i>J. Crystal Growth</i> , 86 , 735-743 (1988) <i>Comment</i> : R, dR. 52 Ions (H-Hg) at 100-700 keV -> CdTe, HgCdTe	1988-Wils2
1989	Tikkanen, P. 'Electronic Stopping Power of Ta for Z=11-18 Atoms at Energies 0-0.8 MeV/amu' <i>Nucl. Inst. Methods</i> , B36 , 103 (1989) <i>Comment</i> : S, Na, Mg, Al, Si, P, S, Cl, Ar (0-0.8 MeV/amu) -> Ta	1989-Tikk
1995	Randhawa, G. S. Garg, A. K. Virk, H. S. 'Range Study of Heavy Ions in Plastic Track Detectors' <i>Rad. Meas. (UK)</i> , 24 , 197-199 (1995) <i>Comment</i> : R. Heavy Ions (10-17 MeV/amu) -> Lexan	1995-Rand
1996	Eriksson, J. Kopniczky, J. Demirev, P. Papaleo, R. M. Brinkmalm, G. 'Damage Cross-Sections and Surface Track Dimensions of Biomolecular Surfaces Bombarded by Swift Heavy Ions' <i>Nucl. Inst. Methods</i> , B107 , 281-286 (1996) <i>Comment</i> : S, S, Cu, Br, I (1.1 cm/ns) -> Biological targets (peptides).	1996-Erik
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. 'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions' <i>Nucl. Inst. Methods</i> , B115 , 315-318 (1996) <i>Comment</i> : S. Channeling of ions He to Kr in Si <110>	1996-Gelf
1996	Hari, K. V. Pathak, A. P. Sharma, S. K. Shyam, K. Nath, N. 'Energy Loss of MeV Heavy Ions in Carbon' <i>Nucl. Inst. Methods</i> , B108 , 223-226 (1996) <i>Comment</i> : S. Zl (O - Cu) at 0.1-1.0 MeV/amu -> C	1996-Hari
2001	Diwan, P. K. Kumar, S. Singh, G. Singh, L. 'Energy Loss of Heavy Ions in Gases: A Comparative Study' <i>Rad. Meas.</i> , 33 , 193-202 (2001) <i>Comment</i> : S, Ne, S, Cl, Ar, Cu, Kr (1 - 80 MeV/u) -> H, He, N, Ar, Ne, Xe, CH ₄ , C ₄ H ₁₀ , CO ₂ , CF ₄	2001-Diwa2
2002	Geissel, H. Weick, H. Scheidenberger, C. Bimbot, R. Gardes, D. 'Experimental Studies of Heavy-Ion Slowing Down in Matter' <i>Nucl. Inst. Methods</i> , B195 , 3-54 (2002) <i>Comment</i> : S. Summary of 18 Heavy Ion Stopping in 26 Targets	2002-Geis

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2007	Sun, G. Döbeli, M. Müller, A.M. Stocker, M. Suter, M. 'Energy loss and straggling of heavy ions in silicon nitride in the low MeV energy range' <i>Nucl. Instrum. Methods B 256 (2007) 586 (2007)</i> <i>Comment : S, dS, Li, B, C, O, S, Fe (0.4 - 4 MeV) ->silicon nitride Si3N3.I</i>	2007-Sun
